

73. The memory card of claim 72, further comprising:
a bottom electrode attached to a second surface of said layer. ✓
74. The memory card of claim 73, wherein said bottom electrode is a common
electrode for said memory storage area. ✓
75. The memory card of claim 72, wherein said memory storage areas comprise ✓
at least one of temporary and permanent memory storage.
76. The memory card of claim 72, wherein said layer comprises chalcogenite. ✓
77. The memory card of claim 72, wherein said layer comprises between 20-30 ✓
percent germanium, between 70 and 80 percent selenium, and is doped with silver.
78. The memory card of claim 73, wherein said bottom electrode further
comprises a conductor such as silver. ✓
79. The memory card of claim 73, wherein said bottom electrode further
comprises a conductor such as tungsten. ✓
80. The memory card of claim 72, wherein said layer further comprises alignment ✓
areas.
81. The memory card of claim 80, wherein said alignment areas are formed as)
memory storage areas programmed with a pattern.
82. The memory card of claim 81, wherein said alignment areas are formed as)
alignment marks.
83. The memory card of claim 72, wherein said memory card has active circuit ✓
elements.

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84. The memory card of claim 72, wherein at least some of said memory storage areas are non volatile. ✓

85. The memory card of claim 72, wherein said first surface of said card is adapted to directly contact said conductive elements. ✓
